NSN 5961-01-120-9314

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-120-9314 **Inclosure Material:** Metal **Overall Length:** 10.463 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-118 **Mounting Method:** Threaded stud **Overall Width Across Flats:** 1.668 inches Thread Size: 0.750 inches **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 1100.0 repetitive peak reverse voltage and 1200.0 nonrepetitive peak reverse voltage and 1000.0 repetitive peak off-state voltage and 470.0 reverse voltage, total rms **Current Rating Per Characteristic:** 470.00 amperes forward current, average megahertz and 11000.00 amperes forward current, average preset **Power Rating Per Characteristic:** 3.0 watts any acceptable universal and 16.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 3 insulated wire lead w/terminal lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: